Complementary Silicon Power Transistors

- ... designed for general-purpose switching and amplifier applications.
- DC Current Gain $h_{FE} = 20-70 @ I_C = 4 Adc$
- Collector–Emitter Saturation Voltage VCE(sat) = 1.1 Vdc (Max) @ IC = 4 Adc
- Excellent Safe Operating Area

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	60	Vdc
Collector–Emitter Voltage	VCER	70	Vdc
Collector–Base Voltage	V _{CB}	100	Vdc
Emitter–Base Voltage	V _{EB}	7	Vdc
Collector Current — Continuous	۱ _C	15	Adc
Base Current	۱ _B	7	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	115 0.657	Watts W/°C
Operating and Storage Junction Temperature Range	TJ, T _{stg}	-65 to +200	°C



*Motorola Preferred Device

15 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 60 VOLTS 115 WATTS



CASE 1-07 TO-204AA (TO-3)

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.52	°C/W



Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.



2N3055 MJ2955

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	_
Collector–Emitter Sustaining Voltage (1) ($I_C = 200 \text{ mAdc}, I_B = 0$)	V _{CEO(sus)}	60	-	Vdc
Collector–Emitter Sustaining Voltage (1) (I _C = 200 mAdc, R _{BE} = 100 Ohms)	V _{CER(sus)}	70	-	Vdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}, I_B = 0$)	ICEO	_	0.7	mAdc
Collector Cutoff Current (V _{CE} = 100 Vdc, V _{BE(off)} = 1.5 Vdc) (V _{CE} = 100 Vdc, V _{BE(off)} = 1.5 Vdc, T _C = 150°C)	ICEX		1.0 5.0	mAdc
Emitter Cutoff Current ($V_{BE} = 7.0 \text{ Vdc}, I_{C} = 0$)	IEBO	_	5.0	mAdc
ON CHARACTERISTICS (1)				
DC Current Gain $(I_C = 4.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$ $(I_C = 10 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$	hFE	20 5.0	70	_
Collector–Emitter Saturation Voltage ($I_C = 4.0 \text{ Adc}, I_B = 400 \text{ mAdc}$) ($I_C = 10 \text{ Adc}, I_B = 3.3 \text{ Adc}$)	VCE(sat)	_	1.1 3.0	Vdc
Base–Emitter On Voltage (I _C = 4.0 Adc, V _{CE} = 4.0 Vdc)	V _{BE(on)}	—	1.5	Vdc
SECOND BREAKDOWN	• •			
Second Breakdown Collector Current with Base Forward Biased (V _{CE} = 40 Vdc, t = 1.0 s, Nonrepetitive)	I _{S/b}	2.87	-	Adc
DYNAMIC CHARACTERISTICS				
Current Gain — Bandwidth Product ($I_C = 0.5 \text{ Adc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ MHz}$)	ŕτ	2.5	-	MHz
*Small–Signal Current Gain (I _C = 1.0 Adc, V _{CE} = 4.0 Vdc, f = 1.0 kHz)	h _{fe}	15	120	
*Small–Signal Current Gain Cutoff Frequency (V _{CE} = 4.0 Vdc, I _C = 1.0 Adc, f = 1.0 kHz)	fhfe	10	-	kHz
				-

* Indicates Within JEDEC Registration. (2N3055)

(1) Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.



Figure 2. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_{C} - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_C = 25^{\circ}C$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 1.



Figure 5. "On" Voltages

PACKAGE DIMENSIONS



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